Minature SMD Reflective Sensor

OPR5005



Features:

- High temperature operation
- Surface mountable
- Compact size
- Excellent ambient light protection



Description:

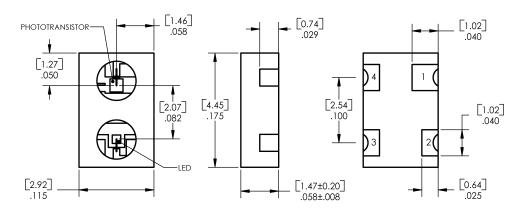
The **OPR5005** is a miniature reflective sensor that combines a silicon phototransistor with a GaAlAs LED in a high-temperature opaque polyamide chip carrier. It is designed to sense the motion or proximity of diffuse reflective surfaces in space-limited applications. The opaque package insures very low cross-talk and shields the phototransistor from ambient light sources, while the silicone encapsulated package allows operation over a wide temperature range. The gold-plated wraparound solder pads offer exceptional storage and wetting characteristics.

See Application Bulletin 237 for handling instructions.

Applications:

- Motion sensors
- Space-limited applications
- Applications requiring ambient light protection
- Can be stored in dirty environments

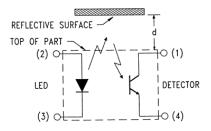
		Orde	ering Inform	nation			
Reflective Switch Part Number	LED Peak Wavelength	Sensor	# of Elements	I _{C(ON)} (μΑ) Min / Typ	I _F (mA) Typ / Max	V _{CE} Typ / Max	Packaging
OPR5005	890 nm	Phototransistor	2	750	20 / 50	5/30	Chip Tray



TOLERANCE IS \pm .005 [0.13] DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Warning: Front Windows are pressure sensitive. Do not apply pressure or high vacuum to window.

Pin#	Description			
1	Collector			
2	Anode			
3	Cathode			
4	Emitter			









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Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)	
Storage and Operating Temperature	-55°C to +125° C
Solder reflow time within 5°C of peak temperature is 20 to 40 seconds ⁽¹⁾	250° C
LED	
Forward DC Current	50 mA
Peak Forward Current (1 μs pulse; .03% duty cycle)	1.0 A
Reverse DC Voltage	2.0 V
Power Dissipation ⁽²⁾	75 mW
Phototransistor	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5.0 V
Collector DC Current	25 mA
Power Dissipation ⁽²⁾	75 mW

Electrical Characteristics (T _A = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
LED							
V_{F}	V _F Forward Voltage		-	1.7	V	I _F = 20 mA	
I _R Reverse Current		-	-	100	μΑ	V _R = 2.0 V	
Phototransistor							
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30	-	-	V	Ι _C = 100 μΑ	
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _Ε = 100 μΑ	
I _{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE} = 5.0 \text{ V, } I_F = 0,$ $E_e = \le 0.10 \mu\text{W/cm}^2$	
Combined							
I _{C(ON)}	On-State Collector Current ⁽⁴⁾	100	-	-	μΑ	V _{CE} = 5.0 V, I _F = 20 mA, d = 0.050" (1.27 mm) ⁽³⁾	
V _{CE(SAT)}	Collector-Emitter Saturation Voltage ⁽⁴⁾	-	-	0.4	V	I _F = 20 mA, I _C = 100 μa, d = 0.050" (1.27 mm) ⁽³⁾	
I _{cx}	Crosstalk ⁽⁵⁾	-	-	75	μΑ	I _F = 20mA, V _{CE} = 5V	

Notes:

- (1) Solder time less than 5 seconds at temperature extreme.
- (2) Derate linearly 0.75 mW/°C above 25°C.
- (3) Distance from the assembly face to the reflective surface is "d".
- (4) Measured using Eastman Kodak neutral white test card with 90% white diffuse reflectance as a reflecting surface.
- (5) Crosstalk (I_{cx}) is the collector current measured using the indicated current and using a Munsell N2.25 black test card against the face of the part.

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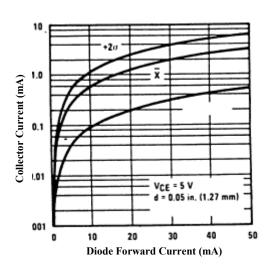
OPR5005



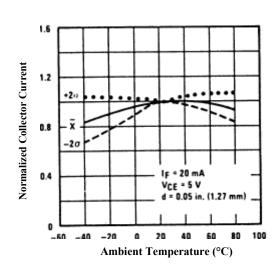
Performance

OPR5005

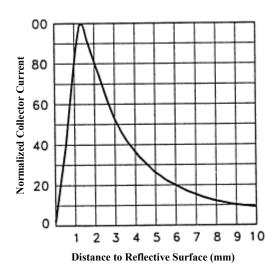
Collector Current vs Diode Forward



Normalized Collector Current vs



Normalized Collector Current vs



Rise and Fall Time vs Load

